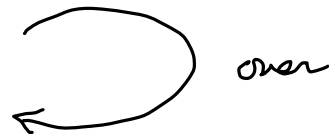


Lecture 12: Mechanics of Materials II

- Announcements:
- HW#3 online and due Tuesday, 2/27, at 10 a.m.
- -----
- Reading: Senturia, Chpt. 8
- Lecture Topics:
- Stress, strain, etc., for isotropic materials
 - ↳ Thin films: thermal stress, residual stress, and stress gradients
 - ↳ Internal dissipation
 - ↳ MEMS material properties and performance metrics
- -----
- Last Time:
- Defined the linear thermal expansion coefficient
- Now, continue with this



Linear Thermal Expansion

temperature \uparrow \rightarrow solids expand in volume

Definition: linear thermal expansion coefficient

$$\left. \begin{array}{l} \text{Linear Thermal} \\ \text{Exp. Coefficient} \end{array} \right\} \cong \alpha_T = \frac{d\epsilon_x}{dT} \quad [\text{Kelvin}^{-1}]$$

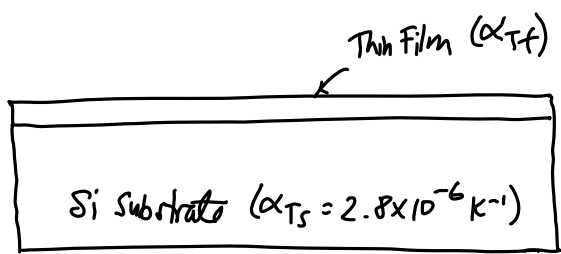
Remarks:

- ① α_T values tend to be in the 10^{-6} to 10^{-7} range
- ② $10^{-6} \text{ K}^{-1} = 1 \mu\text{strain/K}$
- ③ In 3D, get a volume thermal exp. coefficient

$$\frac{\Delta V}{V} = 3\alpha_T \Delta T$$

- ④ For moderate ΔT 's $\rightarrow \alpha_T \approx \text{constant}$
 \downarrow
for large ΔT , then $\alpha_T = f(T)$

Ex. Thin-film Thermal Stress



Assume.

- ① Substrate is much thicker than the film.
- ② Film is deposited stress-free @ T_d . ← deposition temperature
- ③ Then the whole thing is cooled to room temperature, T_r .

Thermal Strain of the Substrate: (in one plane dimension)

$$\epsilon_s = -\alpha_{TS} \Delta T, \text{ where } \Delta T = T_d - T_r$$

If the film were not attached to the substrate:

$$\epsilon_{f, \text{free}} = -\alpha_{TF} \Delta T$$

But the film is attached to the substrate

⇒ thickness substrate \gg thickness of the film
∴ substrate wins!

↓ *

↓ *

thus, the actual strain experienced by the film is that of the substrate:

$$\epsilon_{f, \text{attached}} = -\alpha_{TS} \Delta T$$

Thus:

Thermal Mismatch Strain: $\epsilon_{f, \text{mismatch}} = (\alpha_{TF} - \alpha_{TS}) \Delta T$

↳ Note: This is biaxial strain (assuming the film is deposited isotropically onto the substrate)

$$\sigma_{f, \text{mismatch}} = \underbrace{\left(\frac{E}{1-\nu} \right)}_{E'} \epsilon_{f, \text{mismatch}}$$

Ex. Thin-film is polyimide → $\alpha_{TF} = 70 \times 10^{-6} \text{ K}^{-1}$
 $E' = 4.6 \text{ GPa}$
 deposited @ 250°C , then cooled to $RT = 25^\circ\text{C}$
 $\Delta T = 225 \text{ K}$

$$\epsilon_{f, \text{mismatch}} = (70 - 2.8) \mu (225) = 1.5 \times 10^{-2}$$

[$\mu = 10^{-6}$, $m = 10^{-3}$, $k = 10^3$, $G = 10^9$]

$$\sigma_{f, \text{mismatch}} = (4G)(1.5 \times 10^{-2}) = 60.5 \text{ MPa}$$

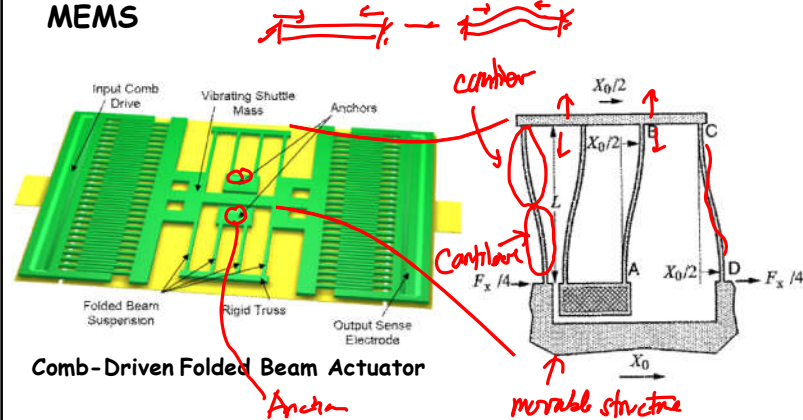
↑
stress is (+) → tensile

[(-) would be compressive]

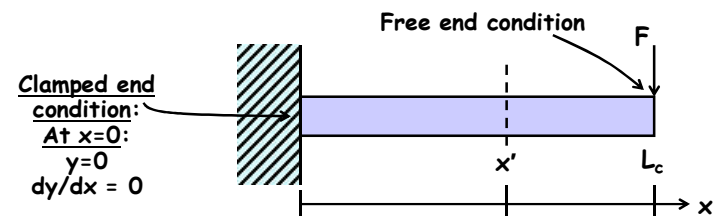
→
SiO₂

- Now go through Module 7 slides 21-55

- Springs and suspensions very common in MEMS
- Coils are popular in the macro-world; but not easy to make in the micro-world
- Beams: simpler to fabricate and analyze; become "stronger" on the micro-scale → use beams for MEMS



Problem: Bending a Cantilever Beam



- **Objective:** Find relation between tip deflection $y(x=L_c)$ and applied load F
- **Assumptions:**
 1. Tip deflection is small compared with beam length
 2. Plane sections (normal to beam's axis) remain plane and normal during bending, i.e., "pure bending"
 3. Shear stresses are negligible

